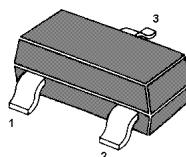


TRANSISTOR (PNP)

SOT-23



- 1. BASE
- 2. EMITTER
- 3. COLLECTOR

MARKING: t2H**

MAXIMUM RATING @ Ta=25°C unless otherwise specified

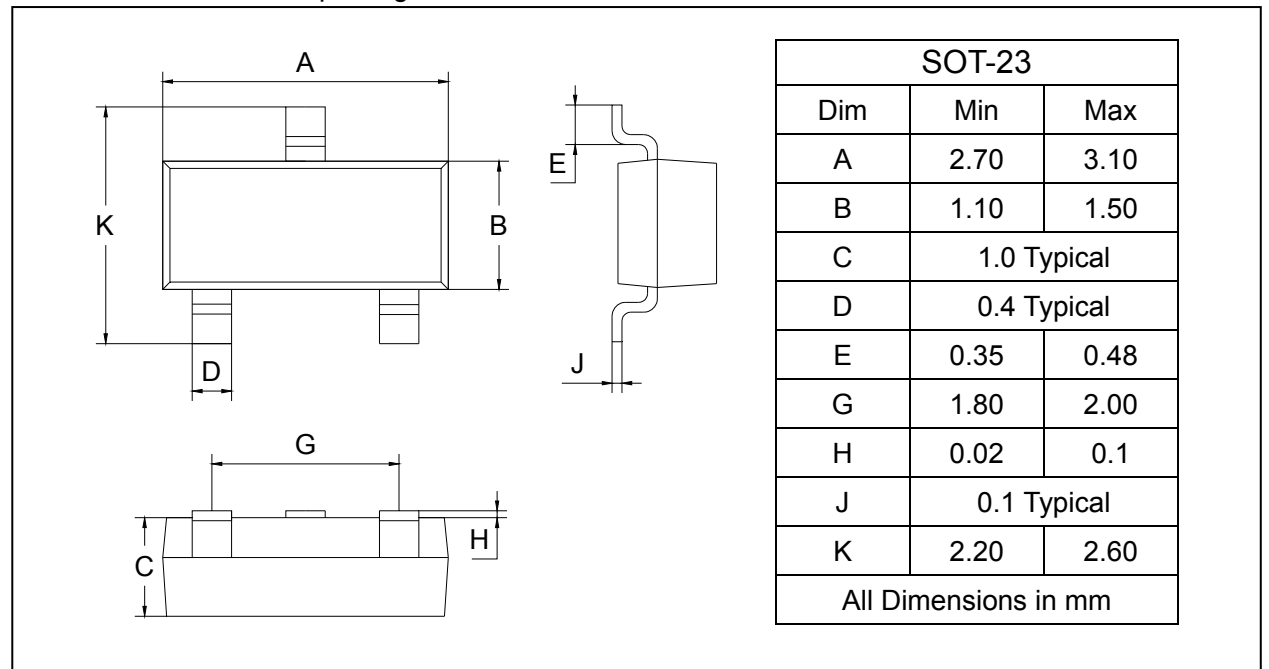
Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-25	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-1.2	A
P_C	Collector Dissipation	0.3	W
T_j, T_{stg}	Junction and Storage Temperature	-55~150	°C

ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

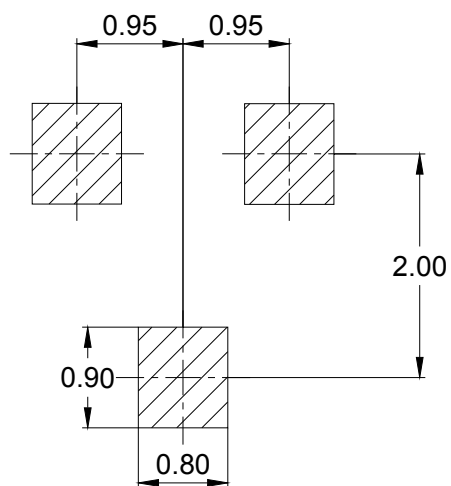
Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu A, I_E = 0$	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -0.1mA, I_B = 0$	-25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu A, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -40V, I_E = 0$			-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = -20V, I_B = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5V, I_C = 0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE} = -1V, I_C = -100mA$	120		400	
		$V_{CE} = -1V, I_C = -800mA$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -800mA, I_B = -80mA$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -800mA, I_B = -80mA$			-1.2	V
Transition frequency	f_T	$V_{CE} = -10V, I_C = -50mA$ $f = 30MHz$	100			MHz
Output capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$			20	pF
Base-emitter voltage	V_{BEF}	$I_E = -1.5A$			-1.6	V

Plastic surface mounted package

SOT-23



SOLDERING FOOTPRINT



Unit : mm

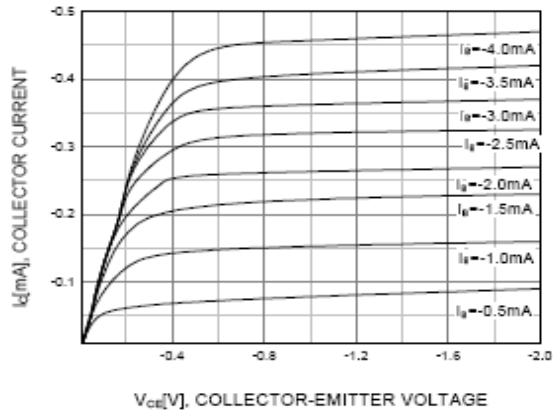


Figure 1. Static Characteristic

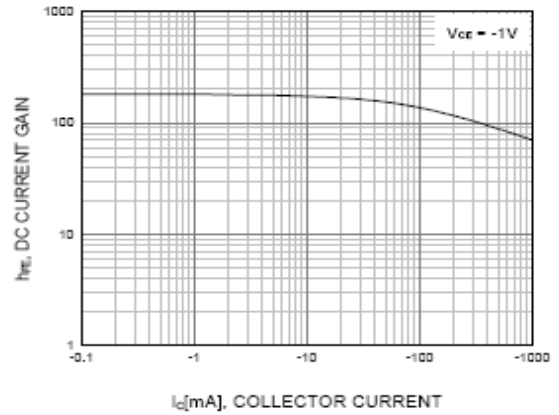


Figure 2. DC current Gain

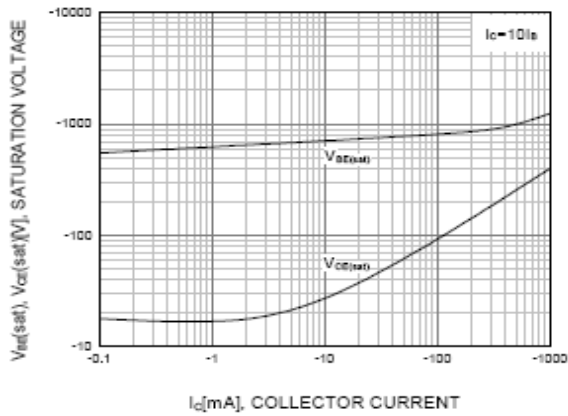


Figure 3. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

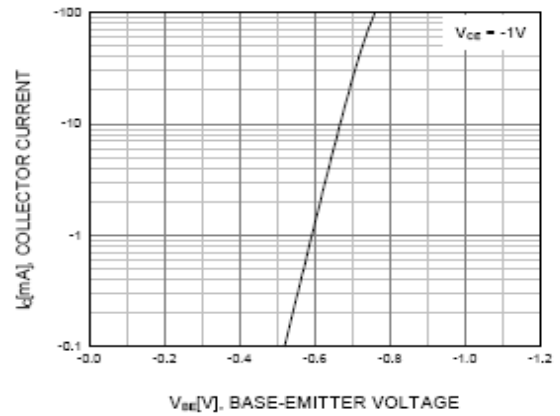


Figure 4. Base-Emitter On Voltage

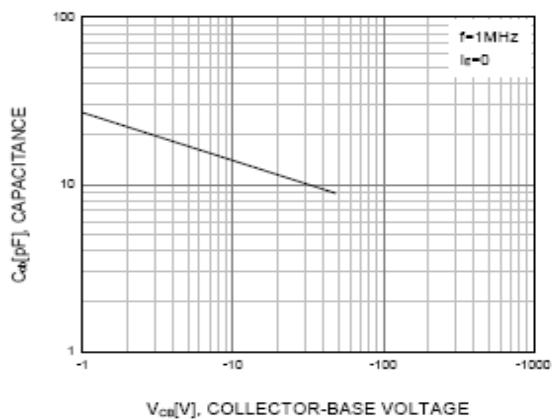


Figure 5. Collector Output Capacitance

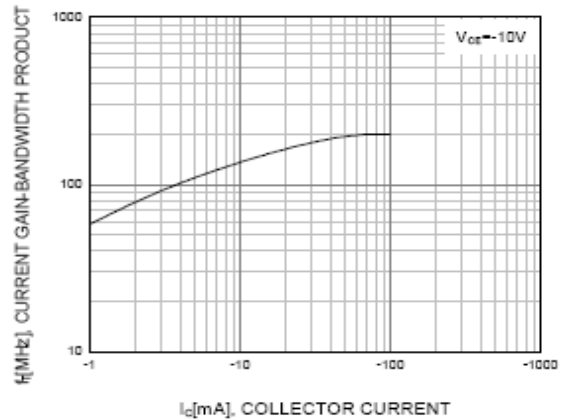


Figure 6. Current Gain Bandwidth Product